Ordering number : ENA0701

SANYO Semiconductors
DATA SHEET

DBG250G — Diffused Junction Silicon Diode
25A Single-Phase Bridge Rectifier

Features

- Glass passivation for high reliability.
- Plastic molded structure.
- Peak reverse voltage : V_{RM}=600V.
- Average output current : I_O=25A.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Peak Reverse Voltage	V_{RM}		600	V
Average Output Current	I_O	Tc=113°C, with heatsink	25	A
		Ta=25°C, without heatsink	3.6	A
Surge Forward Current	I_{FSM}	50Hz sine 1cycle peak value	300	A
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Dilective Strength Voltage	Vdis	Terminals tc case, AC 1 minute	2.5	kV
Tightening Torque	TOR	( ): recommended value	0.8(0.5)	N•m

Electrical Characteristics at Ta=25°C Per Constituent element of bridge.

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Forward Voltage	V_F	I_F=12.5A			0.92	V
Reverse Current	I_R	V_R=600V			10	μA
Thermal Resistance(Junction-Ambient)	Rth(j-a)	Without heatsink			25	°C / W
Thermal Resistance(Junction-Case)	Rth(j-c)	With heatsink			0.8	°C / W
Thermal Resistance(Junction-Lead)	Rth(j-l)	Without heatsink			5	°C / W

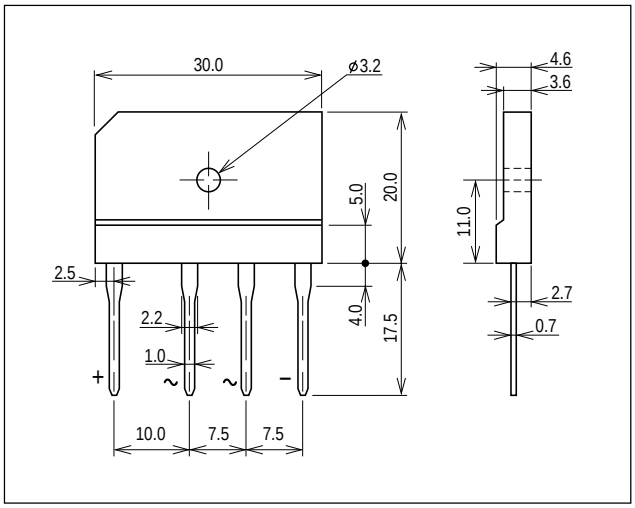
Marking: BG250G

DBG250G

Package Dimensions

unit : mm (typ)

7807-001



Electrical Connection